



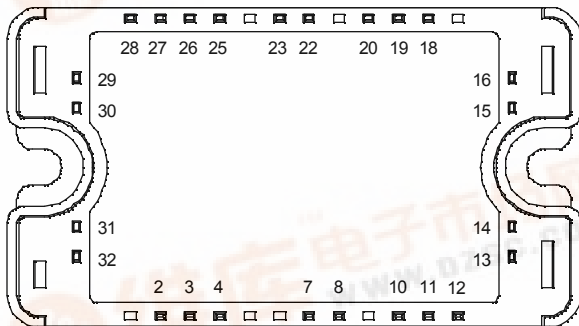
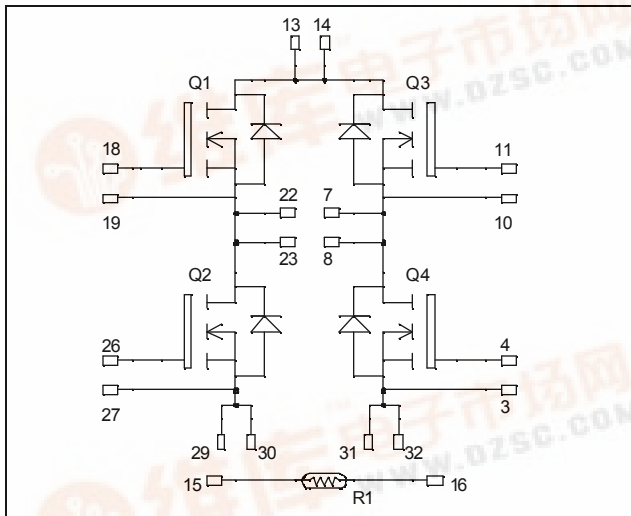
APTC80H29T3

Full - Bridge Super Junction MOSFET Power Module

$$V_{DSS} = 800V$$

$$R_{DSon} = 290m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 15A \text{ @ } T_c = 25^\circ C$$



All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	800	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$ 15 $T_c = 80^\circ C$ 11	A
I_{DM}	Pulsed Drain current	60	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	290	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$ 156	W
I_{AR}	Avalanche current (repetitive and non repetitive)	24	A
E_{AR}	Repetitive Avalanche Energy	0.5	mJ
E_{AS}	Single Pulse Avalanche Energy	670	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	800			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 800V, T_j = 25^\circ\text{C}$			25	μA
		$V_{GS} = 0V, V_{DS} = 800V, T_j = 125^\circ\text{C}$			250	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 7.5A$			290	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1mA$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		2254		pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1046		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		54		
Q_g	Total gate Charge	$V_{GS} = 10V$		90		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 400V$		11		
Q_{gd}	Gate – Drain Charge	$I_D = 15A$		45		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 533V$ $I_D = 15A$ $R_G = 5\Omega$		10		ns
T_r	Rise Time			13		
$T_{d(off)}$	Turn-off Delay Time			83		
T_f	Fall Time			35		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 15A, R_G = 5\Omega$		243		μJ
E_{off}	Turn-off Switching Energy ❷			139		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 533V$ $I_D = 15A, R_G = 5\Omega$		425		μJ
E_{off}	Turn-off Switching Energy ❷			171		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$		15		A
		$T_c = 80^\circ\text{C}$		11		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -15A$			1.2	V
dv/dt	Peak Diode Recovery ❸				6	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -15A$ $V_R = 400V$ $di/dt = 100A/\mu s$	$T_j = 25^\circ\text{C}$	550		ns
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	15		μC

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

❸ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$I_S \leq -15A$ $di/dt \leq 100A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ\text{C}$

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case			0.80	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque		To heatsink	M4	4.7 N.m
Wt	Package Weight			110	g

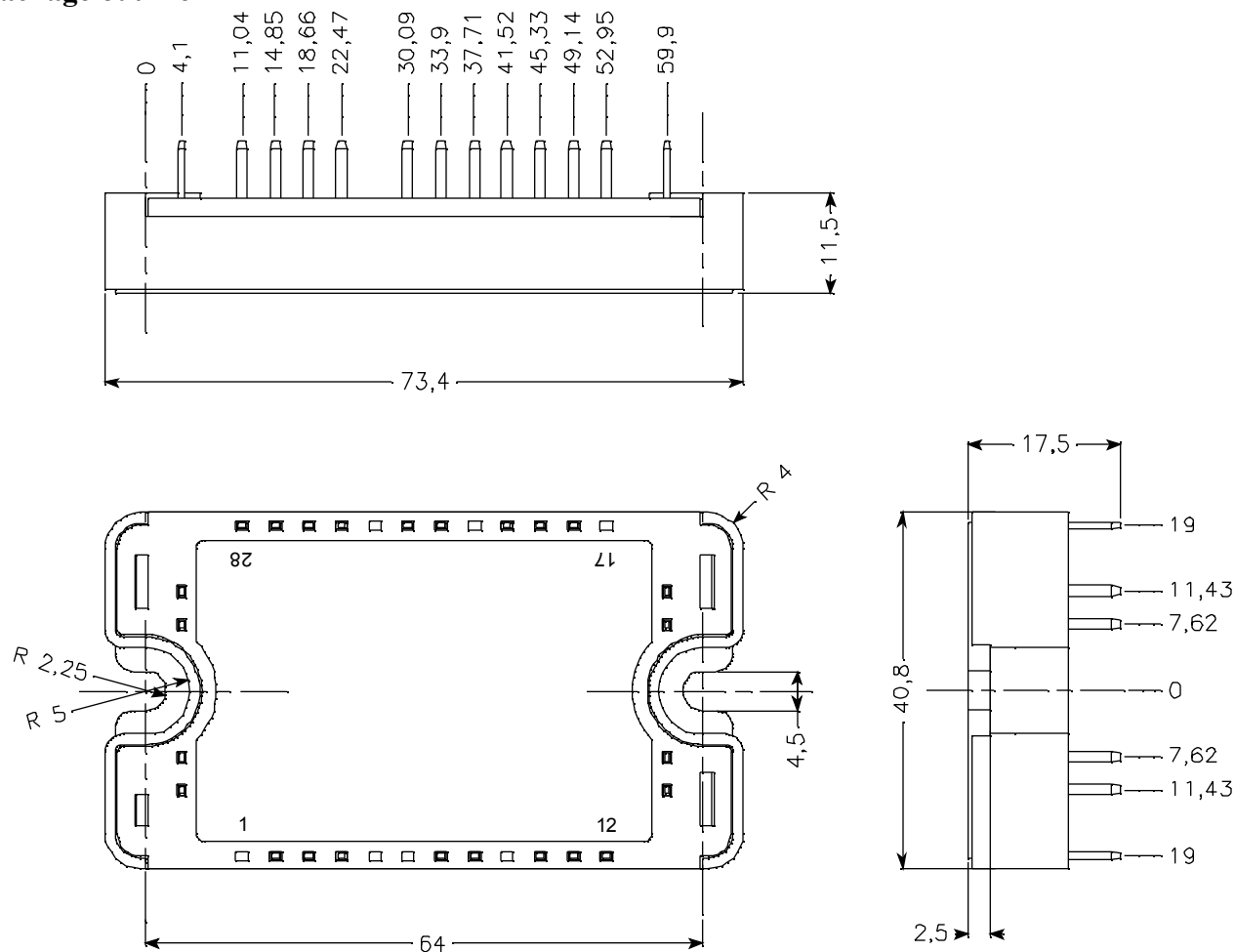
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		68		kΩ
B _{25/85}	T ₂₅ = 298.16 K		4080		K

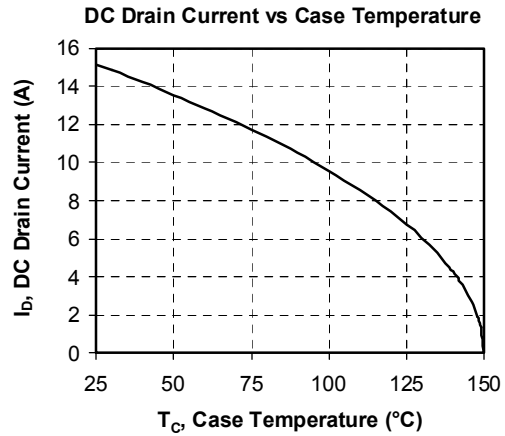
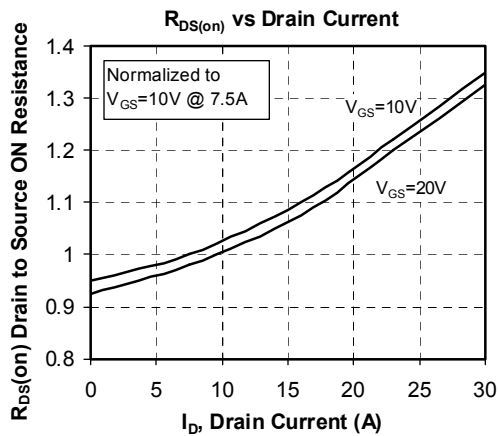
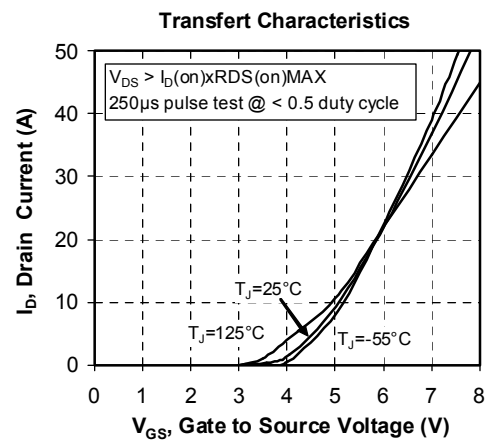
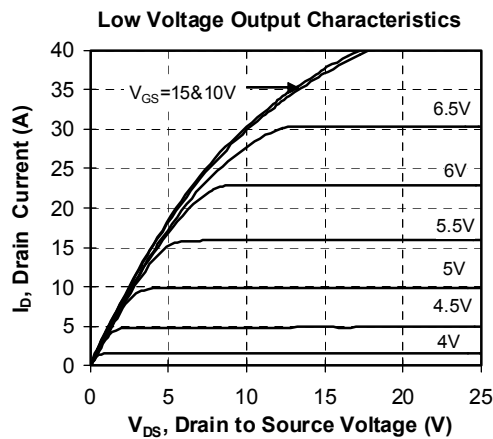
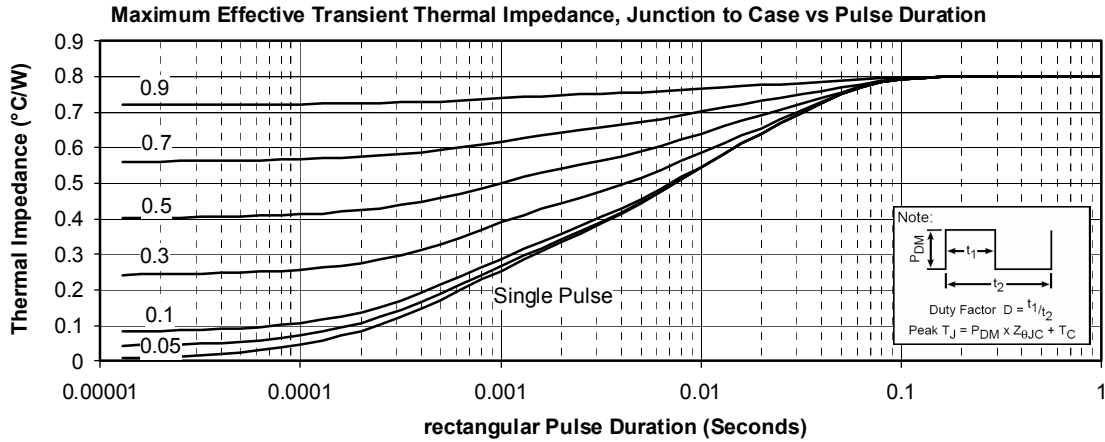
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

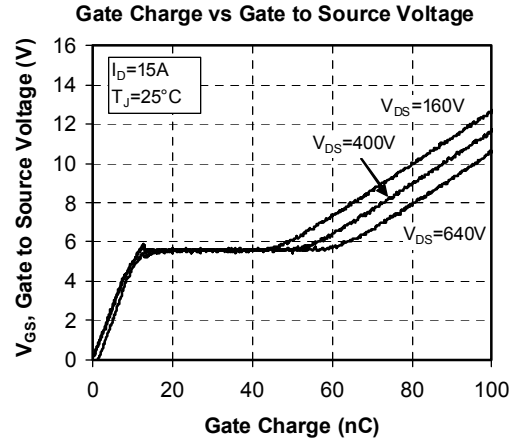
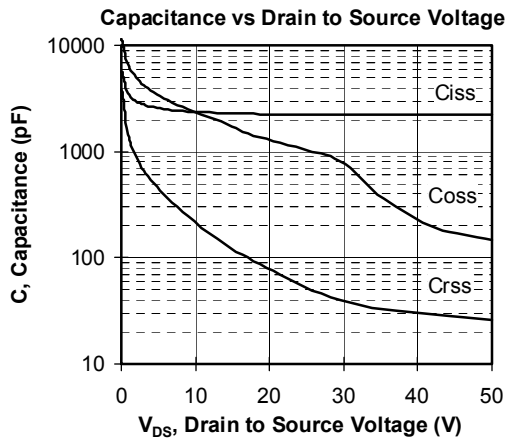
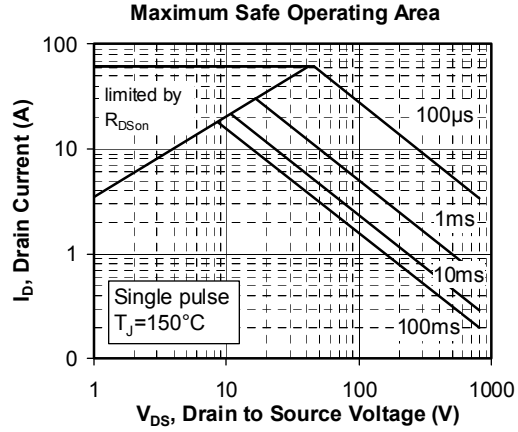
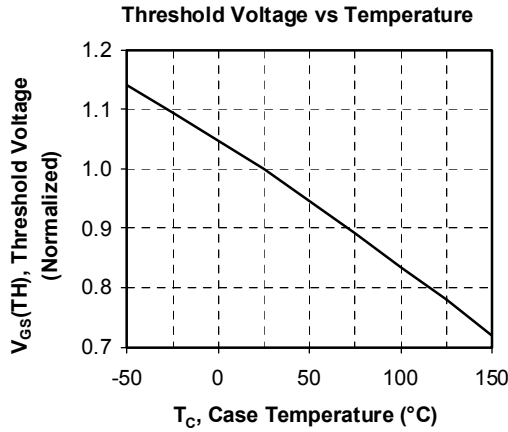
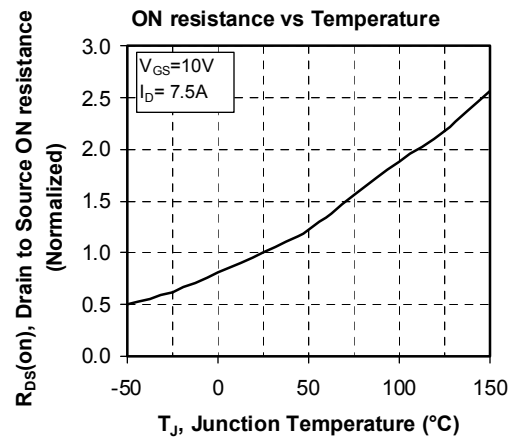
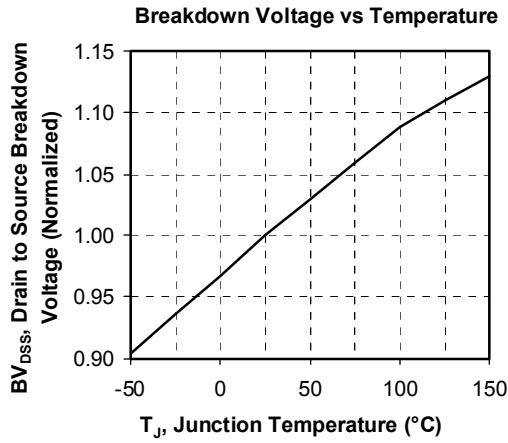
T: Thermistor temperature
R_T: Thermistor value at T

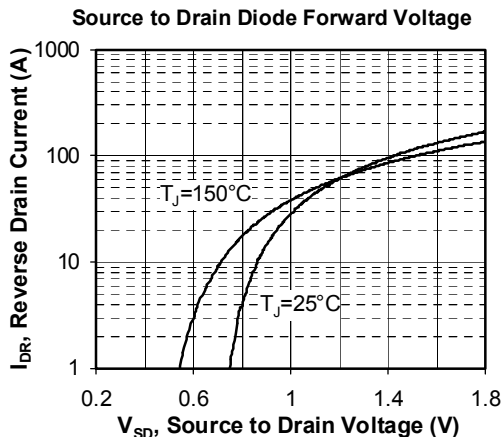
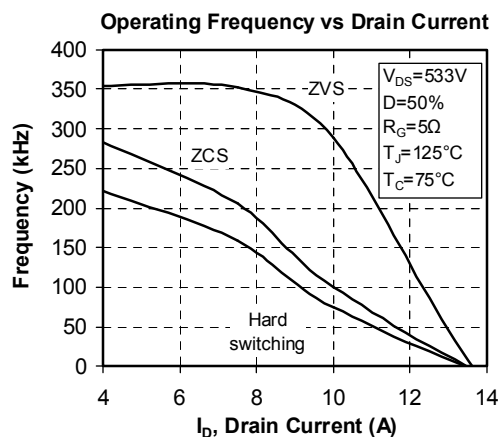
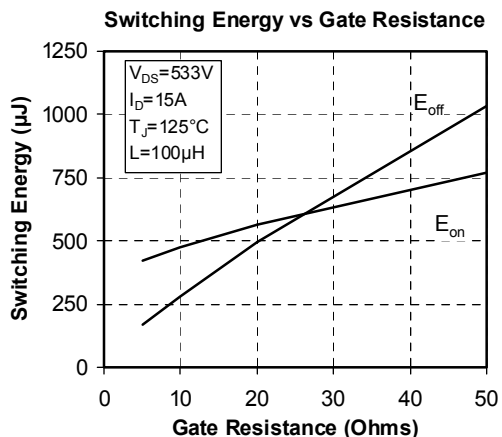
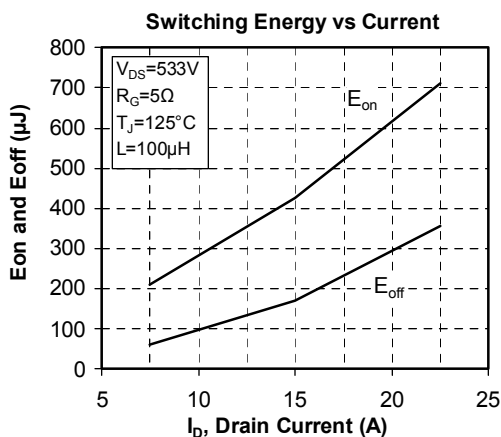
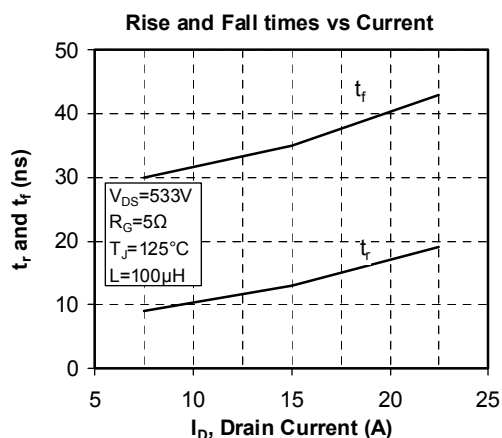
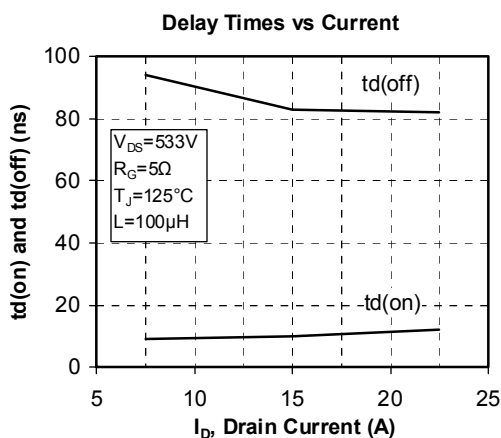
Package outline



Typical performance Curve







“COOLMOST™” comprise a new family of transistors developed by Infineon Technologies AG. “COOLMOS” is a trademark of Infineon Technologies AG”.

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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.